Topological hinge states in Bismuth nanowires revealed by proximity induced superconductivity

A.Murani, B.Dassonneville, A. Kasumov, Shamashis Sengupta,R.Deblock, R.Delagrange, A. Chepelianskii ,H. Bouchiat and S. Guéron LPS Orsay, France

Y. Kasumov, I. Khodos (Chernogolovka)

Proximity effect in material with high spin orbit coupling





Institute of microelectronic tech. and High purity mat.

Normal Superconducting Interface



NS current at eV < Δ

one electron retro-reflected into a hole

Andreev reflection

two electrons passing from N to S

Depends on the transmission of the NS interface

Electron subgap transport in superconducting hybrid systems

398 G 2 2

Les Houches Summer School 2004

« Nanophysics: Coherence and Transport »



Fig. 4. Dimensionless zero-temperature differential conductance $G = dI_{NS}/G_Q dV$, where $G_Q = e^2/\pi\hbar$, as a function of voltage eV/Δ . Curves are off-set for clarity and correspond (from top to bottom) to Z = 0.01, 1.0, and 2.0.

And reev Spectrum of a long SNS junction $L_N > \xi_S$



ballistic junctions rounded with disorder

Revealing topological tranport in Bismuth nanowires

Bulk, surface and edge states

Normal transport: Bulk and Surface states dominant

Superconducting electrodes :

Josephson supercurrent Selects a small number of ballistic edge states

A.Murani PHD thesis april 2017, Nat.Com 2017



Monocrystalline Bismuth nanowires

High quality single crystals

 $\emptyset \sim 100 \, \text{nm}$





Selected Bi Nanowire with 111 surfaces connected with FIB

Electronic structure of Bismuth



Bismuth nanowires

Presence of edge states along 111 surfaces

Anil Murani 2017 : Tight binding simulations



111 Bi bilayer

4

3

 k_x (π/a)



Confined Bi 3D semi metal:

1

2

Α

0.2

0.0

0.2

-0.6

-0.8

-1.0

4

2D metallic surfaces and topological 1D edges

Transport in the normal state T>Tc (electrodes)



Superconducting proximity effect in Bi nanowires T<Tc (electrodes)



Field-dependence of critical supercurrent reveals paths taken by pairs





- Oscillations with field: very few states
- Field direction dependence and period: supercurrent travels at the two acute wire edges
- High field decay scale (oscillations up to 10 Tesla in some samples): narrow channels (nm!).
- High critical current : well transmitted channels.

Current phase relation as a probe of the ballistic nature of transport



Assymetric SQUID

Bi nanowire based SQUID



Current phase relation of a long ballistic SNS junction

Beating between 2 saw tooth





$$I_J(\varphi) = \Sigma \frac{(-1)^n}{n} \sin n\varphi \, t^{2n}$$

Inner edge: 3 channels with t > 0.9 Outer edge: 1 channel with t > 0.7

Effective mean free path > 10 micrometers

Why is the contribution of edge states dominant?

1 ballistic channel $Ic = ev_F/L$

1 diffusive channel Ic = $(I_e/L)^2 ev_F/L$

Surface states $I_e/L \sim 0.1$

NS interface enhanced Andreev reflection of topological helical states

Backward scattering only possible with spin flip



Experimental signatures of topological zero energy level crossing at π



Josephson current: $I_{s}(\phi) = \sum f_{n}(\phi) \ \partial \ \epsilon_{n}(\phi) \ / \ \partial \ \phi$

Finite frequency driving:

$$\begin{split} \phi(t) = \phi_{dc} + \phi_{ac} \cos \omega t \\ \text{Linear response} \\ \delta I (\omega) = \chi(\omega) (\phi_{ac} \exp i\omega t) \\ \chi = i\omega Y = \chi' + i\chi'' \end{split}$$

Probing dynamics of SNS junctions close to equilibrium

Experimental signatures of topoogical zero energy level crossing at pi



Phase dependent finite frequency admittance $Y=\omega\chi$

Diagonal contribution: relaxation of ABS populations

$$\chi_D'' = \frac{\omega \tau_{in}}{(1 + \omega^2 \tau_{in}^2)} \sum_n i_n^2 \frac{\partial f_n}{\partial \epsilon_n}$$





No detectable signal on $f_n(\phi)$...

Phase dependent Quality Factor



$$\delta$$
 (1/Q) = - δ Q/Q² = L_c² / L_R χ"

Coupling inductance $L_c \simeq 100 \text{pH}$ Resonator inductance LR $\simeq 1 \mu \text{H}$

Signature of zero energy Andreev level crossing



Possible fit:

$$\chi_D'' = I^2 \frac{\partial f}{\partial \epsilon} = \frac{(ev_F/L)^2}{4k_B T \cosh^2 \left[\alpha(\phi - \pi)/2k_B T\right]}$$

 $\alpha = ev_F/4L\pi$ Only adjustable parameter $v_F = 4 \ 10^5 \text{ m/s}$ Compatible with dc measurements

Bismuth nanowires with 111 facets

Josephson supercurrent



Carried by a small number of disorder protected edge states

Revealed by SQUID interferometry

Saw tooth current-phase relation Beating between the 2 edges contributions Zeeman field yields phase modulation and 0π transitions

Topological nature of the edges investigated through HF experiments in progress